

**Notice of References Cited**

Application/Control No.

10/540,896

Applicant(s)/Patent Under  
Reexamination  
BUGGE ET AL.

Examiner

JONATHAN C. LANGMAN

Art Unit

1794

Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,798,540	08-1998	Boos et al.	257/194
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Deryagin et al., "High Quality AlGaSb, AlGaAsSb and InGaAsSb epitaxial layers Grown by LPVE from Sb-rich melts", IEE Proceedings., Optoelectronics, Vol. 144, No.6, Dec. 1997, pgs. 438-440.
	V	
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.